



AO4422

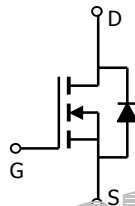
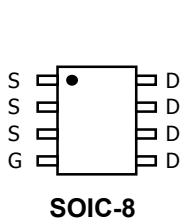
N-Channel Enhancement Mode Field Effect Transistor

General Description

The AO4422 uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. This device is suitable for use as a load switch or in PWM applications. The source leads are separated to allow a Kelvin connection to the source, which may be used to bypass the source inductance.

Features

- V_{DS} (V) = 30V
- I_D = 11A
- $R_{DS(ON)} < 15m\Omega$ ($V_{GS} = 10V$)
- $R_{DS(ON)} < 24m\Omega$ ($V_{GS} = 4.5V$)



Preliminary

Absolute Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ^A	I_D	$T_A = 25^\circ\text{C}$	11
		$T_A = 70^\circ\text{C}$	9.3
Pulsed Drain Current ^B	I_{DM}	70	A
Power Dissipation	P_D	$T_A = 25^\circ\text{C}$	3
		$T_A = 70^\circ\text{C}$	2.1
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	$t \leq 10s$	31	$^\circ\text{C/W}$
Maximum Junction-to-Ambient ^A		Steady-State	59	$^\circ\text{C/W}$
Maximum Junction-to-Lead ^C	$R_{\theta JL}$	16	24	$^\circ\text{C/W}$

Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	$I_D=250\mu\text{A}$, $V_{GS}=0\text{V}$	30			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=24\text{V}$, $V_{GS}=0\text{V}$ $T_J=55^\circ\text{C}$			1	μA
					5	
I_{GSS}	Gate-Body leakage current	$V_{DS}=0\text{V}$, $V_{GS}=\pm 20\text{V}$			100	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$	1	1.8	3	V
$I_{D(ON)}$	On state drain current	$V_{GS}=4.5\text{V}$, $V_{DS}=5\text{V}$	30			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10\text{V}$, $I_D=11\text{A}$ $T_J=125^\circ\text{C}$		12.6	15	m Ω
			$V_{GS}=4.5\text{V}$, $I_D=10\text{A}$		19.6	
g_{FS}	Forward Transconductance	$V_{DS}=5\text{V}$, $I_D=11\text{A}$				S
V_{SD}	Diode Forward Voltage	$I_S=1\text{A}$, $V_{GS}=0\text{V}$		0.76	1	V
I_S	Maximum Body-Diode Continuous Current				4.3	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	$V_{GS}=0\text{V}$, $V_{DS}=15\text{V}$, $f=1\text{MHz}$		1040		pF
C_{oss}	Output Capacitance			180		pF
C_{rss}	Reverse Transfer Capacitance			110		pF
R_g	Gate resistance	$V_{GS}=0\text{V}$, $V_{DS}=0\text{V}$, $f=1\text{MHz}$		0.7		Ω
SWITCHING PARAMETERS						
$Q_g(10\text{V})$	Total Gate Charge	$V_{GS}=10\text{V}$, $V_{DS}=15\text{V}$, $I_D=11\text{A}$				nC
$Q_g(4.5\text{V})$	Total Gate Charge					nC
Q_{gs}	Gate Source Charge					nC
Q_{gd}	Gate Drain Charge					nC
$t_{D(on)}$	Turn-On Delay Time	$V_{GS}=10\text{V}$, $V_{DS}=15\text{V}$, $R_L=1.3\Omega$, $R_{GEN}=3\Omega$				ns
t_r	Turn-On Rise Time					ns
$t_{D(off)}$	Turn-Off Delay Time					ns
t_f	Turn-Off Fall Time					ns
t_{rr}	Body Diode Reverse Recovery Time	$I_F=11\text{A}$, $dI/dt=100\text{A}/\mu\text{s}$				ns
Q_{rr}	Body Diode Reverse Recovery Charge	$I_F=11\text{A}$, $dI/dt=100\text{A}/\mu\text{s}$				nC

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The value in any a given application depends on the user's specific board design. The current rating is based on the $t \leq 10\text{s}$ thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C. The $R_{\theta JA}$ is the sum of the thermal impedance from junction to lead $R_{\theta JL}$ and lead to ambient.

D. The static characteristics in Figures 1 to 6 are obtained using 80 μs pulses, duty cycle 0.5% max.

E. These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The SOA curve provides a single pulse rating.